

Ling-Feng Mao

List of Publications by Year in descending order

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122
papers

1,008
citations

516215

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552369

26
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125
all docs

125
docs citations

125
times ranked

850
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Frequency Selective Surfaces: A Review. Applied Sciences (Switzerland), 2018, 8, 1689. | 1.3 | 178 |
| 2 | Recent advancements in surface plasmon polaritons-plasmonics in subwavelength structures in microwave and terahertz regimes. Digital Communications and Networks, 2018, 4, 244-257. | 2.7 | 51 |
| 3 | DESIGN OF PLANAR DUAL AND TRIPLE NARROW-BAND BANDSTOP FILTERS WITH INDEPENDENTLY CONTROLLED STOPBANDS AND IMPROVED SPURIOUS RESPONSE. Progress in Electromagnetics Research, 2012, 131, 259-274. | 1.6 | 34 |
| 4 | Temperature dependence of the tunneling current in metal-oxide-semiconductor devices due to the coupling between the longitudinal and transverse components of the electron thermal energy. Applied Physics Letters, 2007, 90, 183511. | 1.5 | 31 |
| 5 | Physical Modeling of Activation Energy in Organic Semiconductor Devices based on Energy and Momentum Conservations. Scientific Reports, 2016, 6, 24777. | 1.6 | 31 |
| 6 | Physical unclonable function: architectures, applications and challenges for dependable security. IET Circuits, Devices and Systems, 2020, 14, 407-424. | 0.9 | 31 |
| 7 | The Effects of the Injection-Channel Velocity on the Gate Leakage Current of Nanoscale MOSFETs. IEEE Electron Device Letters, 2007, 28, 161-163. | 2.2 | 26 |
| 8 | The Gate Leakage Current in Graphene Field-Effect Transistor. IEEE Electron Device Letters, 2008, 29, 1047-1049. | 2.2 | 24 |
| 9 | Leakage Power Reduction Techniques of 55 nm SRAM Cells. IETE Technical Review (Institution of) Tj ETQq1 1 0.784314 rgBT / Overload | 2.1 | 24 |
| 10 | A Compact Reconfigurable Bandstop Resonator Using Defected Ground Structure on Coplanar Waveguide. IEEE Antennas and Wireless Propagation Letters, 2012, 11, 457-459. | 2.4 | 21 |
| 11 | Thickness measurements for ultrathin-film insulator metal-oxide-semiconductor structures using Fowler-Nordheim tunneling current oscillations. Journal of Applied Physics, 2000, 88, 6560-6563. | 1.1 | 20 |
| 12 | A NOVEL MINIATURIZED DUAL-BAND BANDSTOP FILTER USING DUAL-PLANE DEFECTED STRUCTURES. Progress in Electromagnetics Research, 2013, 134, 397-417. | 1.6 | 20 |
| 13 | Quantum capacitance of the armchair-edge graphene nanoribbon. Pramana - Journal of Physics, 2013, 81, 309-317. | 0.9 | 19 |
| 14 | A novel combinatorial triangle-type AMC structure for RCS reduction. Microwave and Optical Technology Letters, 2015, 57, 2728-2732. | 0.9 | 18 |
| 15 | Miniaturised frequency selective surface based on fractal arrays with square slots for enhanced bandwidth. IET Microwaves, Antennas and Propagation, 2019, 13, 1811-1819. | 0.7 | 17 |
| 16 | Numerical analysis for root-mean-square roughness of SiO ₂ /Si interface on direct tunneling current in ultrathin MOSFETs. Solid-State Electronics, 2001, 45, 531-534. | 0.8 | 16 |
| 17 | Integrated SRAM compiler with clamping diode to reduce leakage and dynamic power in nano-CMOS process. Micro and Nano Letters, 2012, 7, 171. | 0.6 | 16 |
| 18 | Study of Fowler-Nordheim tunneling current oscillations of thin insulator MOS structure by wave interference method. Solid-State Electronics, 2000, 44, 1501-1506. | 0.8 | 15 |

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|----|--|-----|-----------|
| 19 | The effects of the in-plane momentum on the quantization of nanometer metal-oxide-semiconductor devices due to the difference between the effective masses of silicon and gate oxide. Applied Physics Letters, 2007, 91, 123519. | 1.5 | 15 |
| 20 | Finite size effects on the gate leakage current in graphene nanoribbon field-effect transistors. Nanotechnology, 2009, 20, 275203. | 1.3 | 15 |
| 21 | Enhanced Sparse Regularization Based on Logarithm Penalty and Its Application to Gearbox Compound Fault Diagnosis. IEEE Transactions on Instrumentation and Measurement, 2021, 70, 1-12. | 2.4 | 15 |
| 22 | Physical Modeling of Gate-Controlled Schottky Barrier Lowering of Metal-Graphene Contacts in Top-Gated Graphene Field-Effect Transistors. Scientific Reports, 2015, 5, 18307. | 1.6 | 13 |
| 23 | Investigation of the Correlation Between Temperature and Enhancement of Electron Tunneling Current Through HfO_2 Gate Stacks. IEEE Transactions on Electron Devices, 2008, 55, 782-788. | 1.6 | 10 |
| 24 | The quantum size effects on the surface potential of nanocrystalline silicon thin film transistors. Thin Solid Films, 2010, 518, 3396-3401. | 0.8 | 10 |
| 25 | Finite-Size Effects on Thermionic Emission in Metal-Graphene-Nanoribbon Contacts. IEEE Electron Device Letters, 2010, 31, 491-493. | 2.2 | 10 |
| 26 | A theoretical analysis of field emission from graphene nanoribbons. Carbon, 2011, 49, 2709-2714. | 5.4 | 10 |
| 27 | Miniaturized dual-band bandstop filter using defected microstrip structure and defected ground structure. , 2012, , . | | 10 |
| 28 | The Current Collapse in AlGaIn/GaN High-Electron Mobility Transistors Can Originate from the Energy Relaxation of Channel Electrons?. PLoS ONE, 2015, 10, e0128438. | 1.1 | 10 |
| 29 | Thermionic emission current in graphene-based electronic devices. Applied Physics A: Materials Science and Processing, 2019, 125, 1. | 1.1 | 10 |
| 30 | Quantum coupling and electrothermal effects on electron transport in high-electron mobility transistors. Pramana - Journal of Physics, 2019, 93, 1. | 0.9 | 9 |
| 31 | The effect of image potential on electron transmission and electric current in the direct tunneling regime of ultra-thin MOS structures. Microelectronics Reliability, 2001, 41, 927-931. | 0.9 | 8 |
| 32 | Modeling of temperature dependence of the leakage current through a hafnium silicate gate dielectric in a MOS device. Semiconductor Science and Technology, 2007, 22, 1203-1208. | 1.0 | 8 |
| 33 | A compact quad-band bandstop filter using dual-plane defected structures and open-loop resonators. IEICE Electronics Express, 2012, 9, 1630-1636. | 0.3 | 8 |
| 34 | Modeling of spectral shift in Raman spectroscopy, photo- and electro-luminescence induced by electric field tuning of graphene related electronic devices. Carbon, 2017, 119, 446-452. | 5.4 | 8 |
| 35 | Layer-dependent bandgap and electrical engineering of molybdenum disulfide. Journal of Physics and Chemistry of Solids, 2020, 139, 109331. | 1.9 | 8 |
| 36 | Electromagnetic spectrum chipless radio frequency identification: A review. Digital Communications and Networks, 2020, 6, 377-388. | 2.7 | 8 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 37 | A DFT+U study about agglomeration of Au atoms on reduced surface of rutile TiO ₂ (110). <i>Materials Chemistry and Physics</i> , 2021, 271, 124944. | 2.0 | 8 |
| 38 | Effect of SiO ₂ /Si interface roughness on gate current. <i>Microelectronics Reliability</i> , 2001, 41, 1903-1907. | 0.9 | 7 |
| 39 | Modeling the effects of the channel electron velocity on the channel surface potential of ballistic MOSFETs. <i>Solid-State Electronics</i> , 2008, 52, 186-189. | 0.8 | 7 |
| 40 | Effects of quantum coupling on the performance of metal-oxide-semiconductor field transistors. <i>Pramana - Journal of Physics</i> , 2009, 72, 407-414. | 0.9 | 7 |
| 41 | Effects of Channel Electron In-Plane Velocity on the Capacitance-Voltage Curve of MOS Devices. <i>ETRI Journal</i> , 2010, 32, 68-72. | 1.2 | 7 |
| 42 | A miniaturized dual-frequency Wilkinson power divider using planar artificial transmission lines. , 2010, , . | | 7 |
| 43 | Anisotropic relaxation of a CuO/TiO ₂ surface under an electric field and its impact on visible light absorption: ab initio calculations. <i>Physical Chemistry Chemical Physics</i> , 2015, 17, 17880-17886. | 1.3 | 7 |
| 44 | Graphene-sandwiched silicon structures for greatly enhanced unpolarized light absorption. <i>Optics Communications</i> , 2015, 339, 47-52. | 1.0 | 7 |
| 45 | DFT Calculation about Oxygen Vacancy to Promote Adsorption of a CO Molecule on Single Au-Supported Titanium Dioxide. <i>Physica Status Solidi (B): Basic Research</i> , 2019, 256, 1800386. | 0.7 | 7 |
| 46 | Direct tunneling relaxation spectroscopy in ultra-thin gate oxide MOS structures. <i>Solid-State Electronics</i> , 2000, 44, 2021-2025. | 0.8 | 6 |
| 47 | A compact dual-mode BPF base on interdigital structure. , 2010, , . | | 6 |
| 48 | Interface traps and quantum size effects on the retention time in nanoscale memory devices. <i>Nanoscale Research Letters</i> , 2013, 8, 369. | 3.1 | 6 |
| 49 | Quantum coupling effects on charging dynamics of nanocrystalline memory devices. <i>Microelectronics Reliability</i> , 2014, 54, 404-409. | 0.9 | 6 |
| 50 | Physical origins of the ideality factor of the current equation in Schottky junctions. <i>Pramana - Journal of Physics</i> , 2020, 94, 1. | 0.9 | 6 |
| 51 | Physical origin of kink in GaN HEMTs. <i>Results in Physics</i> , 2021, 30, 104894. | 2.0 | 6 |
| 52 | Stress-induced high-field gate leakage current in ultra-thin gate oxide. <i>Solid-State Electronics</i> , 2000, 44, 977-980. | 0.8 | 5 |
| 53 | Investigating the effects of the interface defects on the gate leakage current in MOSFETs. <i>Applied Surface Science</i> , 2008, 254, 6628-6632. | 3.1 | 5 |
| 54 | Energy distribution of channel electrons and its impacts on the gate leakage current in graphene field-effect transistors. <i>Applied Physics A: Materials Science and Processing</i> , 2010, 98, 565-569. | 1.1 | 5 |

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|----|--|-----|-----------|
| 55 | Mismatch of dielectric constants at the interface of nanometer metal-oxide-semiconductor devices with high-K gate dielectric impacts on the inversion charge density. <i>Pramana - Journal of Physics</i> , 2011, 76, 657-666. | 0.9 | 5 |
| 56 | Dot size effects of nanocrystalline germanium on charging dynamics of memory devices. <i>Nanoscale Research Letters</i> , 2013, 8, 21. | 3.1 | 5 |
| 57 | Current Reduction Caused by the Quantum Coupling of Hot Electrons in AlGaIn/GaN Transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1701035. | 0.8 | 5 |
| 58 | The effect of oxygen vacancy at CO oxidation on anatase (001)-supported single-Au catalyst. <i>Materials Chemistry and Physics</i> , 2020, 240, 122291. | 2.0 | 5 |
| 59 | Novel crest-shaped spoof surface plasmon polaritons for low pass filtering applications. <i>Microwave and Optical Technology Letters</i> , 2020, 62, 1533-1541. | 0.9 | 5 |
| 60 | <i>Asplenium danxiaense</i> sp. nov. (Aspleniaceae, Aspleniineae), a new tetraploid fern species from Guangdong, China, based on morphological and molecular data. <i>European Journal of Taxonomy</i> , 0, 798, 162-173. | 0.6 | 5 |
| 61 | The effect of transition region on the direct tunneling current and Fowler-Nordheim tunneling current oscillations in ultrathin MOS structures. <i>Microelectronics Reliability</i> , 2002, 42, 175-181. | 0.9 | 4 |
| 62 | Low frequency current noise in 2.5 nm MOSFET and fractal dimension of soft breakdown. <i>Solid-State Electronics</i> , 2003, 47, 1451-1456. | 0.8 | 4 |
| 63 | Interaction of oxygen vacancy and its impact on transmission coefficient in oxygen-deficient titanium dioxide: <i>ab initio</i> calculations. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 2735-2744. | 0.7 | 4 |
| 64 | A method to measure the distance among scatters and the scatter's diameter in artificial composite materials. <i>Ultrasonics</i> , 2016, 67, 70-75. | 2.1 | 4 |
| 65 | Impact of Energy Relaxation of Channel Electrons on Drain-Induced Barrier Lowering in Nano-Scale Si-Based MOSFETs. <i>ETRI Journal</i> , 2017, 39, 284-291. | 1.2 | 4 |
| 66 | Metal-substitution strategy to control the conductive path in titanium dioxide: <i>ab initio</i> calculations. <i>European Physical Journal B</i> , 2018, 91, 1. | 0.6 | 4 |
| 67 | Physical Model of the Effects of Drift Velocity on Current Transport in PN Junctions under the Forward Electric Field. <i>Silicon</i> , 2020, 12, 1539-1545. | 1.8 | 4 |
| 68 | Numerical analysis for the effects of SiO ₂ /Si interface roughness on quantum oscillations in ultrathin MOSFETs. <i>Solid-State Electronics</i> , 2001, 45, 773-776. | 0.8 | 3 |
| 69 | Effects of the size of silicon grain on the gate-leakage current in nanocrystalline silicon thin-film transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010, 28, 460-465. | 0.6 | 3 |
| 70 | A compact dual-frequency wilkinson power divider with open-ended stubs. , 2010, , . | | 3 |
| 71 | Quantum size impacts on the threshold voltage in nanocrystalline silicon thin film transistors. <i>Microelectronics Reliability</i> , 2013, 53, 1886-1890. | 0.9 | 3 |
| 72 | First-principles study on defected titanium dioxide with the Zr substitution for improved reliability of the conduction path. <i>EPJ Applied Physics</i> , 2015, 70, 10103. | 0.3 | 3 |

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|----|---|-----|-----------|
| 73 | Structure properties and electrical mechanisms of Si(001)/SiO ₂ interface with varying Si layer thickness in nano-scale transistor. <i>Current Applied Physics</i> , 2018, 18, 1020-1025. | 1.1 | 3 |
| 74 | Electrochemical Modeling of the Effects of F Ions in the AlGa _N Layer on the Two-Dimensional Electron Density in AlGa _N /Ga _N HEMTs. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, P472-P479. | 0.9 | 3 |
| 75 | Novel spoof surface plasmon polaritons on a planar metallic strip with periodic semi-elliptical grooves at microwave frequency. <i>Journal of Electromagnetic Waves and Applications</i> , 2019, 33, 125-137. | 1.0 | 3 |
| 76 | The Dopant Local Effect on the Stability of an Oxygen Vacancy and the Reliability of a Conductive Filament in Rutile Titanium Dioxide. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900455. | 0.7 | 3 |
| 77 | First-Principles investigation on the behavior of Pt single and triple atoms supported on monolayer CuO (1 1 0) in CO oxidation. <i>Applied Surface Science</i> , 2021, 564, 150435. | 3.1 | 3 |
| 78 | First principle studies revealing the effect of O ₂ , CO ₂ , and H ₂ adsorption on field emission behaviour of graphene. <i>Applied Surface Science</i> , 2022, 599, 153938. | 3.1 | 3 |
| 79 | Numerical analysis for the effects of interface roughness on the attenuation amplitudes of Fowler-Nordheim tunneling current oscillations in ultrathin MOSFETs. <i>Solid-State Electronics</i> , 2001, 45, 1081-1084. | 0.8 | 2 |
| 80 | Current-voltage Characteristics of Graphene Nanoribbon Schottky Diodes. <i>IETE Journal of Research</i> , 2012, 58, 65. | 1.8 | 2 |
| 81 | Nature of the Interstitials in Titanium Dioxide and Their Impact on Transmission Coefficient: Ab Initio Calculations. <i>Journal of Nanomaterials</i> , 2015, 2015, 1-9. | 1.5 | 2 |
| 82 | The phononic crystal interface layer determines slow-wave and pulse broadening effects. <i>Turkish Journal of Electrical Engineering and Computer Sciences</i> , 2016, 24, 3759-3768. | 0.9 | 2 |
| 83 | Electrical Double-Layer Modeling of Different Al-Content on the Performance of AlGa _N /Ga _N HEMTs. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, P496-P500. | 0.9 | 2 |
| 84 | Measurements of the widths of transition regions at Si-SiO ₂ interfaces in metal-oxide-semiconductor structures from quantum oscillations in Fowler-Nordheim tunneling current. <i>Solid State Communications</i> , 2001, 119, 67-71. | 0.9 | 1 |
| 85 | An analytical approach to the tunnelling current of MOSFETs considering the barrier height reduction caused by the channel electron velocity due to the effective electron mass difference between silicon and oxide. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007, 204, 3193-3200. | 0.8 | 1 |
| 86 | Effects of Dielectric Constant Mismatch on Capacitance-voltage Curve. <i>IETE Journal of Research</i> , 2009, 55, 218. | 1.8 | 1 |
| 87 | A Low Power Area Efficient Full Custom 3-Read 3-Write General Purpose Register in 65nm Technology. , 2013, , . | | 1 |
| 88 | Energy relaxation of electrons impacts on channel quantization in nano-MOSFETs. <i>Applied Physics A: Materials Science and Processing</i> , 2014, 117, 1835-1840. | 1.1 | 1 |
| 89 | First-principle study on the relaxation of defected titanium dioxide under electric fields and its impacts on capacitor-voltage curves. <i>European Physical Journal B</i> , 2014, 87, 1. | 0.6 | 1 |
| 90 | Effects of Energy Relaxation via Quantum Coupling Among Three-Dimensional Motion on the Tunneling Current of Graphene Field-Effect Transistors. <i>Nanoscale Research Letters</i> , 2015, 10, 1039. | 3.1 | 1 |

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| 91 | The impact of the dopants on the formation of conductive path in titanium dioxide: ab initio calculations. European Physical Journal B, 2016, 89, 1. | 0.6 | 1 |
| 92 | Field emission from Dirac and Weyl semimetals. Applied Physics A: Materials Science and Processing, 2016, 122, 1. | 1.1 | 1 |
| 93 | A Precise Design for Testing High-Speed Embedded Memory using a BIST Circuit. IETE Journal of Research, 2017, 63, 473-481. | 1.8 | 1 |
| 94 | Formation mechanism of conduction path in titanium dioxide with Ti-interstitials-doped: Carâ€Parrinello molecular dynamics. AIP Conference Proceedings, 2017, , . | 0.3 | 1 |
| 95 | Investigation of visibleâ€light absorption in Cu₂O/TiO₂ heterojunctions with an interstitial at the interface. Physica Status Solidi (B): Basic Research, 2017, 254, 1600420. | 0.7 | 1 |
| 96 | Physical origin of the temperature-dependent open-circuit voltage in solar cells. Applied Physics A: Materials Science and Processing, 2020, 126, 1. | 1.1 | 1 |
| 97 | Using modelâ€™s temporal features and hierarchical structure for similar activity recognition. Journal of Ambient Intelligence and Humanized Computing, 2020, , 1. | 3.3 | 1 |
| 98 | Hot-Carriersâ€™ Effect on the Performance of Organic Schottky Diodes. IEEE Access, 2020, 8, 65970-65982. | 2.6 | 1 |
| 99 | An improved method for determining the critical energy for interface trap generation of n-MOSFETs under $V_g=V_d/2$ stress mode. Solid-State Electronics, 2001, 45, 385-389. | 0.8 | 0 |
| 100 | A simple theory to determine the attenuation amplitudes of quantum oscillations. , 0, , . | | 0 |
| 101 | Analysis of Resonant Frequency for Electromagnetic Bandgap Structure Based on Phase Coherence. IETE Journal of Research, 2012, 58, 459. | 1.8 | 0 |
| 102 | Transmission resonant frequency and its amplitude prediction for ebg structure based on phase coherence. Microwave and Optical Technology Letters, 2012, 54, 409-412. | 0.9 | 0 |
| 103 | Research on application of nonlinear system in communication jamming. , 2013, , . | | 0 |
| 104 | THE KINK EFFECTS IN NANO-GaAs DEVICES DUE TO MULTI-VALLEY ELECTRON TRANSPORT. International Journal of Modern Physics B, 2013, 27, 1350172. | 1.0 | 0 |
| 105 | First-principle study on the effects of electric field and anisotropic oxygen vacancy on dielectric properties of rutile titanium dioxide. EPJ Applied Physics, 2014, 68, 10104. | 0.3 | 0 |
| 106 | Time domain characteristics for sub-wavelength defect in one-dimensional structure. , 2015, , . | | 0 |
| 107 | First-Principle Study on the Effects of Electric Field and Oxygen Vacancy on Fine Structure of Rutile Titanium Dioxide and Its Effects on Fowler-Nordheim Tunneling Current in Memory. Journal of Computational and Theoretical Nanoscience, 2015, 12, 2274-2280. | 0.4 | 0 |
| 108 | 28nm latch type sense amplifier coupling effect analysis. , 2016, , . | | 0 |

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|-----|--|-----|-----------|
| 109 | A rectangular patch antenna with wideband high order harmonic suppression using compact defected microstrip structure. , 2016, , . | | 0 |
| 110 | Statistical Analysis of Process Variations on the Delay-Based PUF. , 2016, , . | | 0 |
| 111 | STT MTJ data-aware write boost design in 28nm process. , 2016, , . | | 0 |
| 112 | Modeling of light coupling effect using tunneling theory based on particle properties of light. Optical and Quantum Electronics, 2017, 49, 1. | 1.5 | 0 |
| 113 | Adsorption effect on the formation of conductive path in defective TiO ₂ : ab initio calculations. EPJ Applied Physics, 2017, 80, 10104. | 0.3 | 0 |
| 114 | Quantum scattering and its impact on the source-drain current with defect generation in the channel of nanoscale transistors. Indian Journal of Physics, 2020, 94, 583-592. | 0.9 | 0 |
| 115 | Comparison of the Visible Light Absorption of Titanium Dioxide Photocatalyst with the Ti or Cu Interstitials: Ab Initio Calculations. Journal of Computational and Theoretical Nanoscience, 2017, 14, 1058-1067. | 0.4 | 0 |
| 116 | Conductive Path Along Aggregated O-O Bonds and Its Disruption as Oxygen Vacancy: Ab Initio Calculations. Journal of Computational and Theoretical Nanoscience, 2017, 14, 4377-4383. | 0.4 | 0 |
| 117 | Modeling negative and positive temperature dependence of the gate leakage current in GaN high-electron mobility transistors. ETRI Journal, 0, , . | 1.2 | 0 |
| 118 | Quantum coupling and hot-carriers impacts on excitons and optical spectrum of GaN devices. Physica E: Low-Dimensional Systems and Nanostructures, 2022, 139, 115156. | 1.3 | 0 |
| 119 | Modeling source-drain voltage-dependent energy needed for emission or absorption of a photon in GaN devices. Applied Physics A: Materials Science and Processing, 2022, 128, 1. | 1.1 | 0 |
| 120 | Applying quantum tunnelling concept in the study of the coupling in acoustic waveguides. Results in Physics, 2022, , 105528. | 2.0 | 0 |
| 121 | Monte Carlo simulation of the relationship between intervalley energy difference and electron transport in GaN devices. Pramana - Journal of Physics, 2022, 96, . | 0.6 | 0 |
| 122 | Electron velocity distribution on the abrupt change in source-drain current of GaN devices. International Journal of Modern Physics B, 0, , . | 1.0 | 0 |